

Sanghun Jeon

List of Publications by Year in descending order

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papers

6,619
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81900

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135
docs citations

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times ranked

7622
citing authors

#	ARTICLE	IF	CITATIONS
1	Highly Stretchable Resistive Pressure Sensors Using a Conductive Elastomeric Composite on a Micropyramid Array. <i>Advanced Materials</i> , 2014, 26, 3451-3458.	21.0	1,030
2	Highly stretchable electric circuits from a composite material of silver nanoparticles and elastomeric fibres. <i>Nature Nanotechnology</i> , 2012, 7, 803-809.	31.5	782
3	Gated three-terminal device architecture to eliminate persistent photoconductivity in oxide semiconductor photosensor arrays. <i>Nature Materials</i> , 2012, 11, 301-305.	27.5	434
4	A Flexible Bimodal Sensor Array for Simultaneous Sensing of Pressure and Temperature. <i>Advanced Materials</i> , 2014, 26, 796-804.	21.0	375
5	HfZrO ₂ -Based Ferroelectric Synapse Device With 32 Levels of Conductance States for Neuromorphic Applications. <i>IEEE Electron Device Letters</i> , 2017, 38, 732-735.	3.9	202
6	Effect of hygroscopic nature on the electrical characteristics of lanthanide oxides (Pr ₂ O ₃ , Sm ₂ O ₃), <i>Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50</i>	2.5	150
7	Metal Oxide Thin Film Phototransistor for Remote Touch Interactive Displays. <i>Advanced Materials</i> , 2012, 24, 2631-2636.	21.0	143
8	Amorphous Oxide Semiconductor TFTs for Displays and Imaging. <i>Journal of Display Technology</i> , 2014, 10, 917-927.	1.2	133
9	The effect of the bottom electrode on ferroelectric tunnel junctions based on CMOS-compatible HfO ₂ . <i>Nanotechnology</i> , 2018, 29, 335201.	2.6	120
10	Instability in threshold voltage and subthreshold behavior in Hf _{0.5} In _{0.5} Zn _{0.5} O thin film transistors induced by bias-and light-stress. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	108
11	Low-voltage, high-sensitivity and high-reliability bimodal sensor array with fully inkjet-printed flexible conducting electrode for low power consumption electronic skin. <i>Nano Energy</i> , 2017, 41, 301-307.	16.0	104
12	Oxygen vacancy control as a strategy to achieve highly reliable hafnia ferroelectrics using oxide electrode. <i>Nanoscale</i> , 2020, 12, 9024-9031.	5.6	98
13	Electrical characteristics of ZrO _x Ny prepared by NH ₃ annealing of ZrO ₂ . <i>Applied Physics Letters</i> , 2001, 79, 245-247.	3.3	91
14	Transparent Semiconducting Oxide Technology for Touch Free Interactive Flexible Displays. <i>Proceedings of the IEEE</i> , 2015, 103, 644-664.	21.3	85
15	Paper-Based Bimodal Sensor for Electronic Skin Applications. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 26974-26982.	8.0	83
16	Ultra-thin Hf _{0.5} Zr _{0.5} O ₂ thin-film-based ferroelectric tunnel junction via stress induced crystallization. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	83
17	Nanocrystalline ZnON; High mobility and low band gap semiconductor material for high performance switch transistor and image sensor application. <i>Scientific Reports</i> , 2014, 4, 4948.	3.3	82
18	The Influence of Top and Bottom Metal Electrodes on Ferroelectricity of Hafnia. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 523-528.	3.0	80

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19	A Sensor Array Using Multi-functional Field-effect Transistors with Ultrahigh Sensitivity and Precision for Bio-monitoring. Scientific Reports, 2015, 5, 12705.	3.3	79
20	Nanometer-Scale Oxide Thin Film Transistor with Potential for High-Density Image Sensor Applications. ACS Applied Materials & Interfaces, 2011, 3, 1-6.	8.0	70
21	Insertion of HfO ₂ Seed/Dielectric Layer to the Ferroelectric HZO Films for Heightened Remanent Polarization in MFM Capacitors. IEEE Transactions on Electron Devices, 2020, 67, 745-750.	3.0	67
22	Origin of High Photoconductive Gain in Fully Transparent Heterojunction Nanocrystalline Oxide Image Sensors and Interconnects. Advanced Materials, 2014, 26, 7102-7109.	21.0	65
23	Electrical and physical characteristics of PrTi _x O _y for metal-oxide-semiconductor gate dielectric applications. Applied Physics Letters, 2002, 81, 4856-4858.	3.3	59
24	Flexible Multimodal Sensors for Electronic Skin: Principle, Materials, Device, Array Architecture, and Data Acquisition Method. Proceedings of the IEEE, 2019, 107, 2065-2083.	21.3	59
25	Low-Frequency Noise Performance of a Bilayer InZnO/InGaZnO Thin-Film Transistor for Analog Device Applications. IEEE Electron Device Letters, 2010, 31, 1128-1130.	3.9	58
26	Scalable and facile synthesis of stretchable thermoelectric fabric for wearable self-powered temperature sensors. RSC Advances, 2018, 8, 39992-39999.	3.6	58
27	Sub-60-mV/decade Negative Capacitance FinFET With Sub-10-nm Hafnium-Based Ferroelectric Capacitor. IEEE Journal of the Electron Devices Society, 2017, 5, 306-309.	2.1	57
28	Vertically stacked nanocellulose tactile sensor. Nanoscale, 2017, 9, 17212-17219.	5.6	55
29	Oxygen Defect-Induced Metastability in Oxide Semiconductors Probed by Gate Pulse Spectroscopy. Scientific Reports, 2015, 5, 14902.	3.3	53
30	Ar plasma treated ZnON transistor for future thin film electronics. Applied Physics Letters, 2015, 107, .	3.3	52
31	Effects of high pressure nitrogen annealing on ferroelectric Hf _{0.5} Zr _{0.5} O ₂ films. Applied Physics Letters, 2018, 112, .	3.3	52
32	Pulse Switching Study on the HfZrO Ferroelectric Films With High Pressure Annealing. IEEE Transactions on Electron Devices, 2018, 65, 1771-1773.	3.0	52
33	Enhanced tunneling electroresistance effects in HfZrO-based ferroelectric tunnel junctions by high-pressure nitrogen annealing. Applied Physics Letters, 2018, 113, .	3.3	51
34	High-Performance Nanowire Oxide Photo-Thin Film Transistor. Advanced Materials, 2013, 25, 5549-5554.	21.0	49
35	Verification of Interface State Properties of a-InGaZnO Thin-Film Transistors With SiN_x and SiO_2 Gate Dielectrics by Low-Frequency Noise Measurements. IEEE Electron Device Letters, 2011, 32, 1083-1085.	3.9	48
36	Enhancement of resistive switching properties in Al ₂ O ₃ bilayer-based atomic switches: multilevel resistive switching. Nanotechnology, 2018, 29, 235202.	2.6	46

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37	Effect of Forming Gas High-Pressure Annealing on Metal-Ferroelectric-Semiconductor Hafnia Ferroelectric Tunnel Junction. IEEE Electron Device Letters, 2020, 41, 1193-1196.	3.9	43
38	Modeling Sub-Threshold Current-Voltage Characteristics in Thin Film Transistors. Journal of Display Technology, 2013, 9, 883-889.	1.2	42
39	Short channel device performance of amorphous InGaZnO thin film transistor. Applied Physics Letters, 2011, 99, .	3.3	41
40	Ferroelectricity Enhancement in $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Based Tri-Layer Capacitors at Low-Temperature (350 Å°C) Annealing Process. IEEE Electron Device Letters, 2021, 42, 812-815.	3.9	39
41	The impact of active layer thickness on low-frequency noise characteristics in InZnO thin-film transistors with high mobility. Applied Physics Letters, 2012, 100, .	3.3	38
42	Demonstration of High Ferroelectricity ($P_r \sim 29 \text{ } \mu\text{C}/\text{cm}^2$) in Zr Rich $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$ Films. IEEE Electron Device Letters, 2020, 41, 34-37.	3.9	38
43	Robust and scalable three-dimensional spacer textile pressure sensor for human motion detection. Smart Materials and Structures, 2019, 28, 065019.	3.5	37
44	Excellent Reliability and High-Speed Antiferroelectric HfZrO_2 Tunnel Junction by a High-Pressure Annealing Process and Built-In Bias Engineering. ACS Applied Materials & Interfaces, 2020, 12, 57539-57546.	8.0	37
45	Beneficial effect of hydrogen in aluminum oxide deposited through the atomic layer deposition method on the electrical properties of an indium-gallium-zinc oxide thin-film transistor. Journal of Information Display, 2016, 17, 65-71.	4.0	36
46	High-k $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$, Ferroelectric Insulator by Utilizing High Pressure Anneal. IEEE Transactions on Electron Devices, 2020, 67, 2489-2494.	3.0	36
47	Influence of Hf contents on interface state properties in HfInZnO thin-film transistors with $\text{SiN}_x/\text{SiO}_x$ gate dielectrics. Applied Physics Letters, 2011, 99, .	3.3	32
48	Photosensitivity of InZnO thin-film transistors using a solution process. Applied Physics Letters, 2016, 109, .	3.3	30
49	Insertion of Dielectric Interlayer: A New Approach to Enhance Energy Storage in $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$, Capacitors. IEEE Electron Device Letters, 2021, 42, 331-334.	3.9	30
50	Crystalline Phase-Controlled High-Quality Hafnia Ferroelectric With RuO_2 , Electrode. IEEE Transactions on Electron Devices, 2020, 67, 3431-3434.	3.0	29
51	Effect of Insertion of Dielectric Layer on the Performance of Hafnia Ferroelectric Devices. IEEE Transactions on Electron Devices, 2021, 68, 841-845.	3.0	29
52	The Influence of Hydrogen on Defects of InGaZnO Semiconductor Thin-Film Transistors With Atomic-Layer Deposition of Al_2O_3 . IEEE Electron Device Letters, 2016, 37, 1131-1134.	3.9	28
53	Selector-less Ferroelectric Tunnel Junctions by Stress Engineering and an Imprinting Effect for High-Density Cross-Point Synapse Arrays. ACS Applied Materials & Interfaces, 2021, 13, 59422-59430.	8.0	28
54	Influence of High-Pressure Annealing Conditions on Ferroelectric and Interfacial Properties of Zr-Rich $\text{Hf}_x\text{Zr}_{1-x}\text{O}_2$, Capacitors. IEEE Transactions on Electron Devices, 2021, 68, 1996-2002.	3.0	27

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55	Stress Engineering as a Strategy to Achieve High Ferroelectricity in Thick Hafnia Using Interlayer. IEEE Transactions on Electron Devices, 2021, 68, 2538-2542.	3.0	27
56	Poly-4-vinylphenol (PVP) and Poly(melamine-co-formaldehyde) (PMF)-Based Atomic Switching Device and Its Application to Logic Gate Circuits with Low Operating Voltage. ACS Applied Materials & Interfaces, 2017, 9, 27073-27082.	8.0	25
57	High mobility and high stability glassy metal-oxynitride materials and devices. Scientific Reports, 2016, 6, 23940.	3.3	24
58	Transparent and Flexible Mayan-Pyramid-based Pressure Sensor using Facile-Transferred Indium tin Oxide for Bimodal Sensor Applications. Scientific Reports, 2019, 9, 14040.	3.3	24
59	Fast transient charging behavior of HfInZnO thin-film transistor. Applied Physics Letters, 2015, 107, .	3.3	23
60	Electrical characteristics of a Dy-doped HfO ₂ gate dielectric. Applied Physics Letters, 2001, 79, 2615-2617.	3.3	22
61	Evolution of crystallographic structure and ferroelectricity of Hf _{0.5} Zr _{0.5} O ₂ films with different deposition rate. AIP Advances, 2020, 10, .	1.3	22
62	Flexible Ferroelectric Hafnia-Based Synaptic Transistor by Focused-Microwave Annealing. ACS Applied Materials & Interfaces, 2022, 14, 1326-1333.	8.0	22
63	Fully transparent InGaZnO thin film transistors using indium tin oxide/graphene multilayer as source/drain electrodes. Applied Physics Letters, 2010, 97, .	3.3	21
64	Flexible multimodal sensor inspired by human skin based on hair-type flow, temperature, and pressure. Flexible and Printed Electronics, 2020, 5, 025003.	2.7	21
65	Field-induced macroscopic barrier model for persistent photoconductivity in nanocrystalline oxide thin-film transistors. Applied Physics Letters, 2014, 104, .	3.3	20
66	Defects and Charge-Trapping Mechanisms of Double-Active-Layer In ₂ O ₃ and Al ₂ O ₃ /ZnO/In ₂ O ₃ Thin-Film Transistors. ACS Applied Materials & Interfaces, 2017, 9, 9271-9279.	8.0	20
67	Amorphous FeZr metal for multi-functional sensor in electronic skin. Npj Flexible Electronics, 2019, 3, .	10.7	18
68	Improved Ferroelectric Switching in Sputtered HfZrO _x Device Enabled by High Pressure Annealing. IEEE Electron Device Letters, 2020, 41, 232-235.	3.9	18
69	Impact of transparent electrode on photoresponse of ZnO-based phototransistor. Applied Physics Letters, 2013, 103, 251111.	3.3	17
70	III-V compound semiconductors for mass-produced nano-electronics: theoretical studies on mobility degradation by dislocation. Scientific Reports, 2016, 6, 22001.	3.3	17
71	Anomalous high photoconductivity in short channel indium-zinc-oxide photo-transistors. Applied Physics Letters, 2015, 106, .	3.3	16
72	Influence of Fast Charging on Accuracy of Mobility in InHfZnO Thin-Film Transistor. IEEE Electron Device Letters, 2017, 38, 203-206.	3.9	16

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73	Low-Temperature Growth of Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ Thin Films Assisted by Deep Ultraviolet Light Irradiation. ACS Applied Electronic Materials, 2021, 3, 1244-1251.	4.3	16
74	Sub 5 Å...-EOT Hf _{0.5} Zr _{0.5} O ₂ , for Next-Generation DRAM Capacitors Using Morphotropic Phase Boundary and High-Pressure (200 atm) Annealing With Rapid Cooling Process. IEEE Transactions on Electron Devices, 2022, 69, 103-108.	3.0	16
75	The influence of interfacial defects on fast charge trapping in nanocrystalline oxide-semiconductor thin film transistors. Semiconductor Science and Technology, 2016, 31, 055014.	2.0	15
76	High Performance and High Endurance HfO ₂ -Based Ferroelectric Field Effect Transistor Memory with a Spherical Recess Channel. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100018.	2.4	15
77	Effect of high pressure anneal on switching dynamics of ferroelectric hafnium zirconium oxide capacitors. Journal of Applied Physics, 2021, 129, .	2.5	15
78	Photoresponse of an oxide semiconductor photosensor. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, .	1.2	14
79	Excellent Resistive Switching Performance of Cu-Se-Based Atomic Switch Using Lanthanide Metal Nanolayer at the Cu-Se/Al ₂ O ₃ Interface. ACS Applied Materials & Interfaces, 2018, 10, 8124-8131.	8.0	14
80	Quantitative analysis of charge trapping and classification of sub-gap states in MoS ₂ TFT by pulse $I-V$ method. Nanotechnology, 2018, 29, 175704.	2.6	14
81	Trade-off between interfacial charge and negative capacitance effects in the Hf-Zr-Al-O/Hf _{0.5} Zr _{0.5} O ₂ bilayer system. Solid-State Electronics, 2020, 174, 107914.	1.4	14
82	Effect of hydrogen on dynamic charge transport in amorphous oxide thin film transistors. Nanotechnology, 2016, 27, 325203.	2.6	13
83	Resistive switching characteristics of a modified active electrode and Ti buffer layer in Cu Se-based atomic switch. Journal of Alloys and Compounds, 2018, 753, 551-557.	5.5	13
84	High Performance and Self-rectifying Hafnia-based Ferroelectric Tunnel Junction for Neuromorphic Computing and TCAM Applications. , 2021, , .		13
85	High performance low voltage amorphous oxide TFT Enhancement/Depletion inverter through uni-/bi-layer channel hybrid integration. , 2009, , .		12
86	Thickness dependent low-frequency noise characteristics of a -InZnO thin-film transistors under light illumination. Applied Physics Letters, 2014, 104, 023505.	3.3	12
87	First-order reversal curve diagrams for characterizing ferroelectricity of Hf _{0.5} Zr _{0.5} O ₂ films grown at different rates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, .	1.2	12
88	Electrical characteristics of ultrathin ZrO ₂ prepared by wet oxidation of an ultrathin Zr-metal layer. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 400.	1.6	11
89	Fast and slow transient charging of Oxide Semiconductor Transistors. Scientific Reports, 2017, 7, 11850.	3.3	10
90	Influence of High-Pressure Annealing on Memory Properties of Hf _{0.5} Zr _{0.5} O ₂ Based 1T-FeRAM. IEEE Electron Device Letters, 2019, 40, 1076-1079.	3.9	10

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91	Electrical characteristics of ZrO ₂ prepared by electrochemical anodization of Zr in an ammonium tartrate electrolyte. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, L5-L9.	2.1	9
92	Pulse I-V characterization of a nano-crystalline oxide device with sub-gap density of states. Nanotechnology, 2016, 27, 215203.	2.6	9
93	Polymer-Assisted Solution Processing of TiO ₂ Thin Films for Resistive-Switching Random Access Memory. Journal of the Electrochemical Society, 2017, 164, H21-H24.	2.9	9
94	Comprehensive study of high pressure annealing on the ferroelectric properties of Hf _{0.5} Zr _{0.5} O ₂ thin films. Nanotechnology, 2019, 30, 505204.	2.6	9
95	Improved optical performance of multi-layer MoS ₂ phototransistor with see-through metal electrode. Nano Convergence, 2019, 6, 32.	12.1	9
96	Ferroelectricity in Al _f /Hf _{0.5} Zr _{0.5} O ₂ Bilayer Stack: Role of Dielectric Layer Thickness and Annealing Temperature. Journal of Semiconductor Technology and Science, 2021, 21, 62-67.	0.4	9
97	Impact of fast transient charging and ambient on mobility of WS ₂ field-effect transistor. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	8
98	Ferroelectricity Enhancement in Hf _{0.5} Zr _{0.5} O ₂ Capacitors by Incorporating Ta ₂ O ₅ Dielectric Seed Layers. , 2020, , .		8
99	Efficient Suppression of Defects and Charge Trapping in High Density In-Sn-Zn-O Thin Film Transistor Prepared using Microwave-Assisted Sputter. ACS Applied Materials & Interfaces, 2017, 9, 36962-36970.	8.0	8
100	Oxide electronics: Translating materials science from lab-to-fab. MRS Bulletin, 2021, 46, 1028-1036.	3.5	8
101	Microsecond Pulse I-V Approach to Understanding Defects in High Mobility Bi-layer Oxide Semiconductor Transistor. Scientific Reports, 2017, 7, 8235.	3.3	7
102	Non-Volatile Majority Function Logic Using Ferroelectric Memory for Logic in Memory Technology. IEEE Electron Device Letters, 2022, 43, 1049-1052.	3.9	7
103	High performance ferroelectric field-effect transistors for large memory-window, high-reliability, high-speed 3D vertical NAND flash memory. Journal of Materials Chemistry C, 2022, 10, 9802-9812.	5.5	7
104	Excellent electrical characteristics of lanthanide (Pr, Nd, Sm, Gd, and Dy) oxide and lanthanide-doped oxide for MOS gate dielectric applications. , 0, , .		6
105	Non-volatile resistive switching in CuBi-based conductive bridge random access memory device. Applied Physics Letters, 2018, 112, 253503.	3.3	6
106	Metal-induced n/n homojunction for ultrahigh electron mobility transistors. NPG Asia Materials, 2020, 12, .	7.9	6
107	Relatively Low-k Ferroelectric Nonvolatile Memory Using Fast Ramping Fast Cooling Annealing Process. IEEE Transactions on Electron Devices, 2022, 69, 3439-3445.	3.0	6
108	Effect of dysprosium and lutetium metal buffer layers on the resistive switching characteristics of Cu-Sn alloy-based conductive-bridge random access memory. Nanotechnology, 2018, 29, 385207.	2.6	5

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109	Enabling large ferroelectricity and excellent reliability for ultra-thin hafnia-based ferroelectrics with a W bottom electrode by inserting a metal-nitride diffusion barrier. Applied Physics Letters, 2021, 119, .	3.3	5
110	Determination of intrinsic mobility of a bilayer oxide thin-film transistor by pulsed I^2V method. Nanotechnology, 2017, 28, 175201.	2.6	4
111	(Invited) Hafnia Ferroelectric Device for Semiconductor, Sensor, and Display Applications. ECS Transactions, 2020, 98, 219-223.	0.5	4
112	A Monte Carlo simulation for bipolar resistive memory switching in large band-gap oxides. Applied Physics Letters, 2015, 107, .	3.3	3
113	Wearable pressure sensor based on solution-coated fabric for pulse detection. , 2022, , .		3
114	Dislocation effects in FinFETs for different III-V compound semiconductors. Journal Physics D: Applied Physics, 2016, 49, 155101.	2.8	2
115	Effect of High Pressure Annealing Temperature on the Ferroelectric Properties of $\text{TiN}/\text{Hf}_{0.25}\text{Zr}_{0.75}\text{O}_2/\text{TiN}$ Capacitors. , 2020, , .		2
116	Metallic Glass-Based Dual-Mode Sensor for Soft Electronics. IEEE Sensors Journal, 2020, 20, 12396-12401.	4.7	2
117	Silk-Based Self Powered Pressure Sensor for Applications in Wearable Device. , 2020, , .		2
118	Effect of Hydrogen on Hafnium Zirconium Oxide Fabricated by Atomic Layer Deposition Using H_2O_2 Oxidant. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100020.	2.4	2
119	Effect of Ga composition on mobility in a-InGaZnO thin-film transistors. Nanotechnology, 2021, 32, 095201.	2.6	2
120	Vertical Pillar Ferroelectric Field-Effect Transistor Memory. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	2.4	2
121	Flexible and stretchable conductive fabric for temperature detection. , 2022, , .		2
122	Highly Manufacturable Device Isolation Technology Using Laser-Induced Epitaxial Growth for Monolithic Stack Devices. IEEE Transactions on Electron Devices, 2011, 58, 3863-3868.	3.0	1
123	Fourier spectrum based extraction of an equivalent trap state density in indium gallium zinc oxide transistors. Applied Physics Letters, 2014, 104, 203505.	3.3	1
124	Flexible Multi-Modal Sensor for Electronic Skin. , 2019, , .		1
125	Electrical Characteristics of TaOxNy for High-k MOS Gate Dielectric Applications. Materials Research Society Symposia Proceedings, 2000, 611, 1.	0.1	0
126	Oxide electronics for imaging and displays. , 2013, , .		0

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127	A combinatorial device analysis method of oxide thin-film transistors. , 2015, , .		0
128	45.3: <i>Invited Paper</i>: High Performance Nanocrystalline ZnO _x N _y for Imaging and Display Applications. Digest of Technical Papers SID International Symposium, 2015, 46, 681-684.	0.3	0
129	Oxide thin film transistor technology: Capturing device-circuit interactions. , 2015, , .		0
130	Light illumination effect in AlZTO/IZO dual-channel TFTs. , 2016, , .		0
131	Discharge Current Analysis Estimating the Defect Sites in Amorphous Hafnia Thin-Film Transistor. IEEE Transactions on Electron Devices, 2018, 65, 3264-3268.	3.0	0
132	Opportunity of Metallic Glass in Soft Electronics. , 2019, , .		0
133	Broad spectral responsivity in highly photoconductive InZnO/MoS ₂ heterojunction phototransistor with ultrathin transparent metal electrode. Nanotechnology, 2020, 31, 035201.	2.6	0
134	Interfacial Dipole Modulation Device With SiO _x Switching Species. IEEE Journal of the Electron Devices Society, 2021, 9, 57-60.	2.1	0
135	Nano-Crystalline Oxide Semiconductor Materials for Display and Semiconductor Device Applications. ECS Meeting Abstracts, 2014, , .	0.0	0